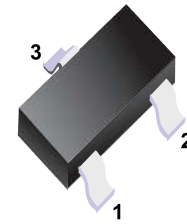


■ PNP Silicon Epitaxial Transistor

■ Features

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications



1.Base
2.Emitter
3.Collector

■ Simplified outline(SOT-523)

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	80	V
		50	
		30	
Collector Emitter Voltage	-V _{CEO}	65	V
		45	
		30	
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	100	mA
Peak Collector Current	-I _{CM}	200	mA
Power Dissipation	P _{tot}	150	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 65 to + 150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Min.	Max.	Unit	
DC Current Gain at $-V_{CE} = 5\text{ V}$, $-I_C = 2\text{ mA}$	Current Gain Group A	h_{FE}	125	250	-
	B	h_{FE}	220	475	-
	C	h_{FE}	420	800	-
Collector Base Cutoff Current at $-V_{CB} = 30\text{ V}$	$-I_{CBO}$	-	15	nA	
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	BC856T	$-V_{(BR)CBO}$	80	-	V
	BC857T, BC860T	$-V_{(BR)CBO}$	50	-	
	BC858T, BC859T	$-V_{(BR)CBO}$	30	-	
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	BC856T	$-V_{(BR)CES}$	80	-	V
	BC857T, BC860T	$-V_{(BR)CES}$	50	-	
	BC858T, BC859T	$-V_{(BR)CES}$	30	-	
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$	BC856T	$-V_{(BR)CEO}$	65	-	V
	BC857T, BC860T	$-V_{(BR)CEO}$	45	-	
	BC858T, BC859T	$-V_{(BR)CEO}$	30	-	
Emitter Base Breakdown Voltage at $-I_E = 1\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	V	
Collector Emitter Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 0.5\text{ mA}$ at $-I_C = 100\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{CE(sat)}$	-	0.3	V	
	$-V_{CE(sat)}$	-	0.65		
Base Emitter On Voltage at $-I_C = 2\text{ mA}$, $-V_{CE} = 5\text{ V}$ at $-I_C = 10\text{ mA}$, $-V_{CE} = 5\text{ V}$	$-V_{BE(on)}$	0.6	0.75	V	
	$-V_{BE(on)}$	-	0.82		
Current Gain Bandwidth Product at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	100	-	MHz	
Collector Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	6	pF	

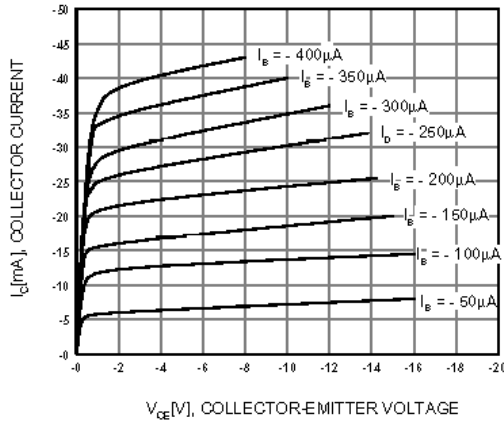


Figure 1. Static Characteristic

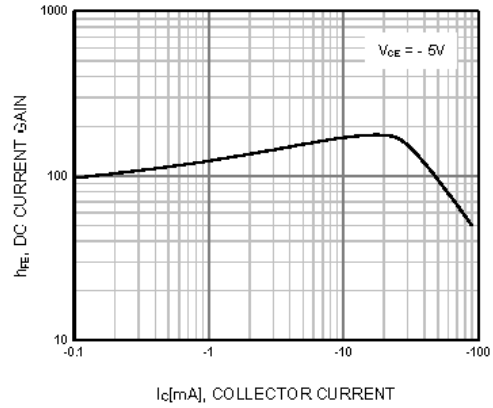


Figure 2. DC current Gain

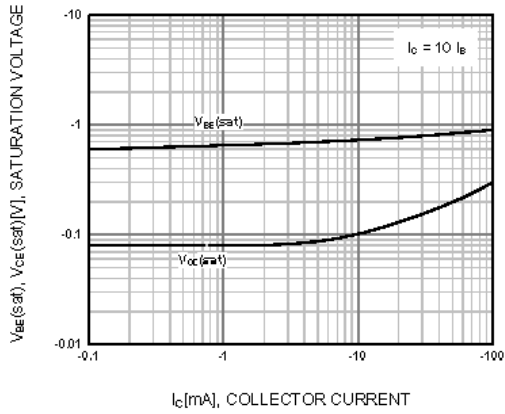


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

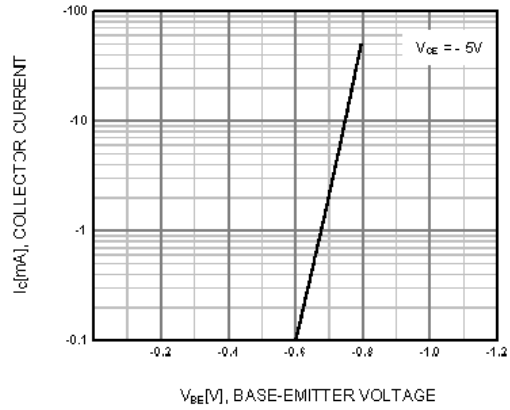


Figure 4. Base-Emitter On Voltage

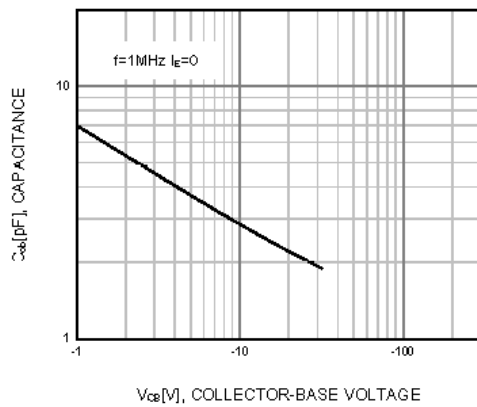


Figure 5. Collector Output Capacitance

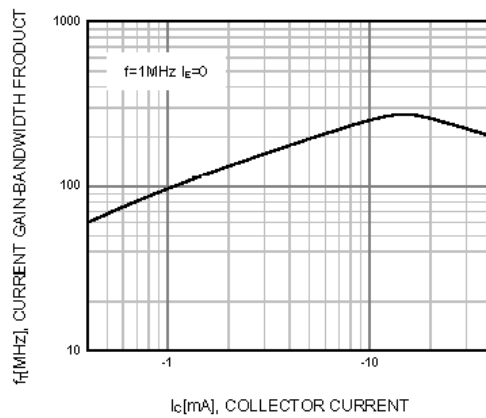
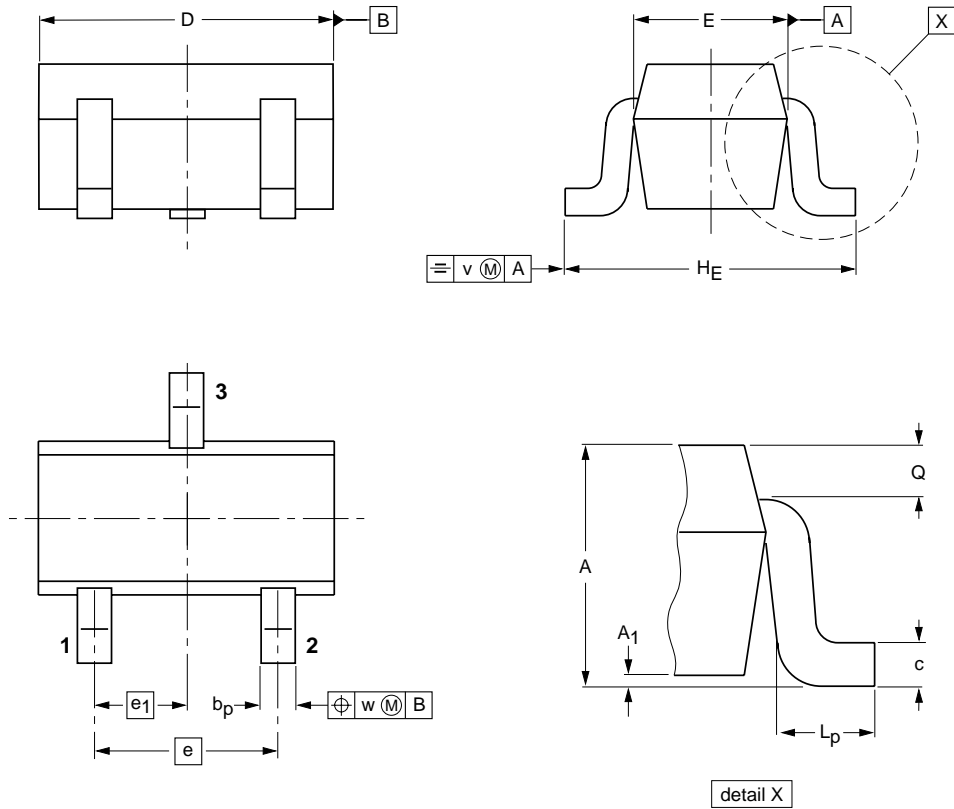


Figure 6. Current Gain Bandwidth Product



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

Summary of Packing Options

Package	Packing Description	Packing Quantity	Industry Standard
SOT-523	Tape/Reel,7"reel	3000	EIA-481-1